

Form PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
M130-068SERIAL NO.
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Ji Ung Lee et al.FILING DATE
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10/10/2015
027/05/02

U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclasses	Filing Date if Appropriate
V4	AA	5,482,870	01/09/86	Inoue			
X	AB	5,372,973	12/13/94	Doan et al.			
	AC	5,229,331	07/20/93	Doan et al.			
	AD	5,210,472	05/11/93	Casper et al.			
	AE	4,988,638	01/29/91	Huang et al.			
	AF	6,057,555	5/2/00	Reedy et al.			
	AG	5,710,478	1/20/98	Kanemaru et al.			
V	AH	6,020,683	2/1/00	Cathay, Jr. et al.			
V4	AI	6,249,327 B1	6/19/01	Murade et al.			
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclasses	Translation	
							Yes	No
V4	AL	5-114734	05/07/93	Japan			X	
X	AM	3-194937	08/26/91	Japan			X	
	AN	3-159250	07/09/91	Japan			X	
	AO	A-2-143482	11/24/88	Japan			X	
V	AP	61-252687	11/10/88	Japan			X	
V4	AQ	A-57-85262	11/17/80	Japan			X	

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

V4	AR		Polycrystalline Silicon Thin Film Transistor Incorporating a Semi-Insulating Field Plate for High Voltage Circuitry on Glass,
			F.J. Clough, E.M.S. Narayanan, Y. Chen, W. Eccleston, and W.I. Milne, Appl. Phys. Lett. 71 - 10/06/97, pages 2002-2004, 1997 American Institute of Physics.
V4	AS		Geometry Dependence of the Transport Parameters in Field Effect Transistors Made From Amorphous Silicon, S. Gilep, Mat. Res. Soc. Symp. Proc. 149, pages 283-288, 1989 Materials Research Society.
	AT		

EXAMINER

V. Yuzovkov

DATE CONSIDERED

04/26/05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.